

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
6 March 2003 (06.03.2003)

PCT

(10) International Publication Number
WO 03/019623 A3

(51) International Patent Classification⁷: H01L 21/336, 29/76, 29/94

(21) International Application Number: PCT/US02/27189

(22) International Filing Date: 23 August 2002 (23.08.2002)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data: 09/938,253 23 August 2001 (23.08.2001) US

(71) Applicant: GENERAL SEMICONDUCTOR, INC. [US/US]; 10 Melville Park Road, Melville, NY 11747 (US).

(72) Inventors: BLANCHARD, Richard, A.; 10724 Mora Drive, Los Altos, CA 94024 (US). HSHIEH, Fwu-Iuan; 20768 Sevilla Lane, Saratoga, CA 95070 (US). SO, Koon, Chong; 591 Woodview Terrace, Fremont, CA 94539 (US).

(74) Agent: WILLIAMS, Karin, L.; Mayer Fortkort & Williams, PC, 251 North Avenue West, 2nd floor, Westfield, NJ 07909 (US).

(81) Designated States (national): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VN, YU, ZA, ZM, ZW.

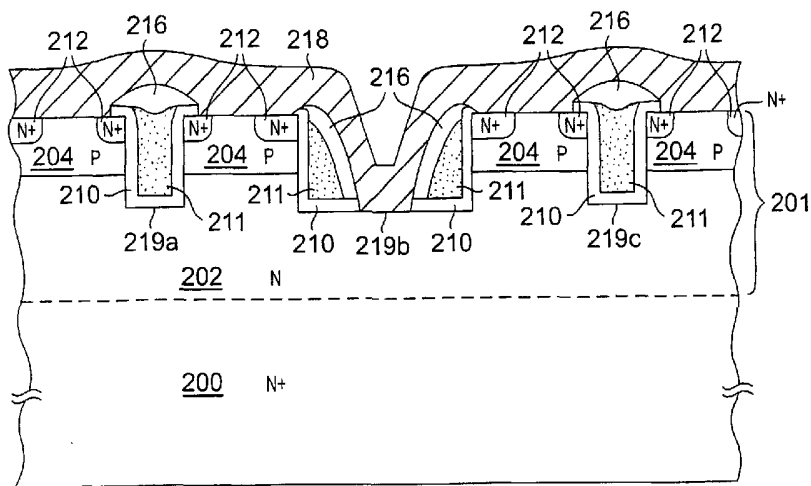
(84) Designated States (regional): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published: — with international search report

(88) Date of publication of the international search report: 16 October 2003

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: TRENCH DMOS TRANSISTOR WITH EMBEDDED TRENCH SCHOTTKY RECTIFIER



(57) Abstract: A merged device is that comprises a plurality of MOSFET cells (19) and a plurality of Schottky rectifier cells (S), as well as a method of designing and making the same. According to an embodiment of the invention, the MOSFET cells comprise: (a) a source region (212) of first conductivity type formed within an upper portion of a semiconductor region (201), (b) a body region (204) of second conductivity type formed within a middle portion of the semiconductor region (201), (c) a drain region (202) of first conductivity type formed within a lower portion of the semiconductor region (201), and (d) a gate region (211) positioned adjacent the source region (212), the body region (204), and the drain region (202). The Schottky diode cells (S) in this embodiment are disposed within a trench network (219a, 219b, 219c) and comprise a conductor portion (218) in Schottky rectifying contact with the lower portion of the semiconductor region (201). At least one MOSFET cell gate region (211) is positioned along a sidewall of the trench network (219a, 219b, 219c) and adjacent at least one Schottky diode cell (S) in this embodiment.



WO 03/019623 A3

INTERNATIONAL SEARCH REPORT

International application No.

PCT/US02/27189

A. CLASSIFICATION OF SUBJECT MATTER		
IPC(7) : H01L 21/336, 29/76, 29/94		
US CL : 438/268,270,272; 257/328,329,331		
According to International Patent Classification (IPC) or to both national classification and IPC		
B. FIELDS SEARCHED		
Minimum documentation searched (classification system followed by classification symbols) U.S. : 438/268,270,272; 257/328,329,331		
Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched NONE		
Electronic data base consulted during the international search (name of data base and, where practicable, search terms used) EAST		
C. DOCUMENTS CONSIDERED TO BE RELEVANT		
Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	US 6,049,108 A (Williams et al.) 11 April 2000 (11.04.2000), column 7, line 20 through column 8, line 11.	1-8, 10-15, 24-27
X, P	US 6,351,018 B1 (Sapp) 26 February 2002 (26.02.2002), column 3, line 45 through column 5, line 63.	1-8, 10-15, 24-27
<input type="checkbox"/> Further documents are listed in the continuation of Box C. <input type="checkbox"/> See patent family annex.		
* Special categories of cited documents:		
"A"	document defining the general state of the art which is not considered to be of particular relevance	"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention
"E"	earlier application or patent published on or after the international filing date	"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone
"L"	document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)	"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art
"O"	document referring to an oral disclosure, use, exhibition or other means	"&" document member of the same patent family
"P"	document published prior to the international filing date but later than the priority date claimed	
Date of the actual completion of the international search 28 January 2003 (28.01.2003)		Date of mailing of the international search report 26 FEB 2003
Name and mailing address of the ISA/US Commissioner of Patents and Trademarks Box PCT Washington, D.C. 20231 Facsimile No. (703)305-3230		Authorized officer <i>Sham S. Hozze</i> Olik Chaudhuri Telephone No. 703-308-0956